

PTO-1449

ATTORNEY'S DKT NO.
025219-268

APPLICATION No.
09/600,590

APPLICANT
Bernard Aspar, et al.

FILING DATE
July 19, 2000

GROUP
Unassigned

U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE

FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No
KIK	FR 2861472	Mar. 1993	FR			/	
KIK	EP 0412002	Feb. 1991	EP			/	

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

1C1C	Y.H. Lo "New approach to grow pseudomorphic structures over the critical thickness", <i>1991 American Institute of Physics, pp.2311-2313.</i>
1C1C	J.F. Klem, et al. "Characterization of thin AlGaAs/InGaAs/GaAs quantum-well structures bonded directly to SiO ₂ /Si and glass substrates", <i>1989 American Institute of Physics, pp.459-462.</i>
1C1C	F.E. Ejeckam, et al. "Dislocation-free InSb grown on GaAs compliant universal substrates", <i>1997 American Institute of Physics, pp. 776-778.</i>
EXAMINER	DATE CONSIDERED
JK RK	10-18-02

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.